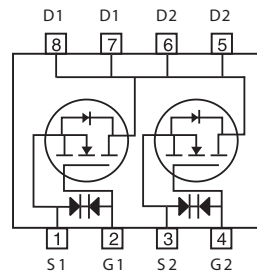
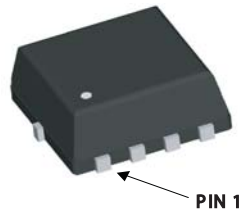


**Dual N-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	12A	9.5 @ V _{GS} =4.5V
		9.8 @ V _{GS} =4.0V
		10.5 @ V _{GS} =3.8V
		12.5 @ V _{GS} =3.1V
		15.0 @ V _{GS} =2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

S mini 8**ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)**

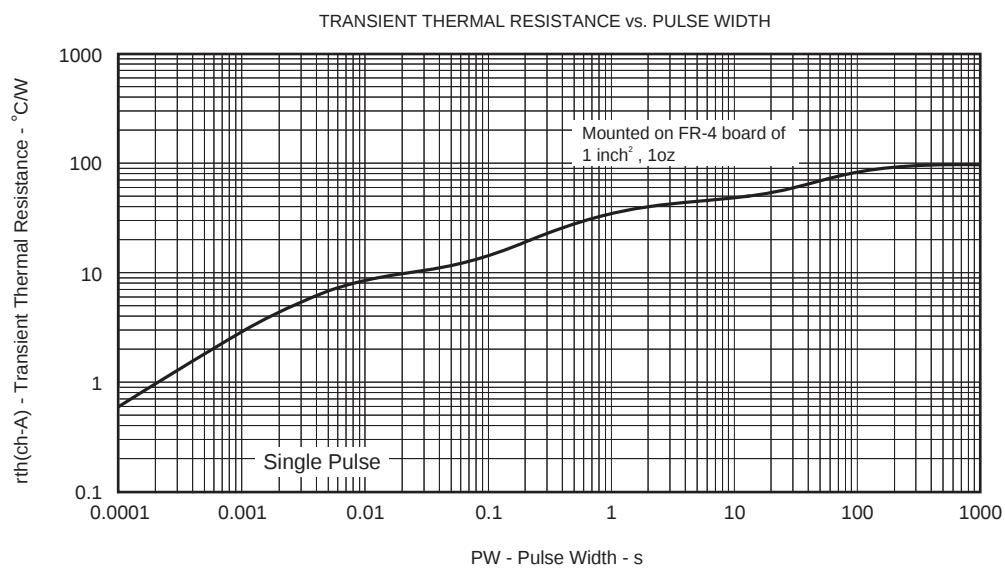
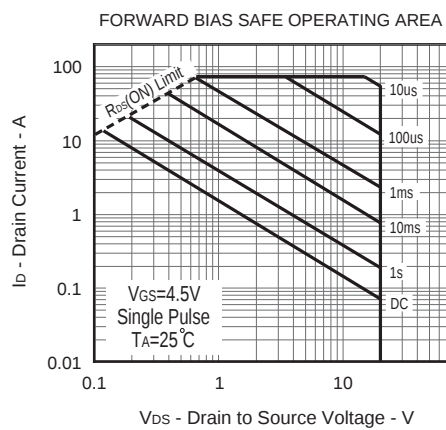
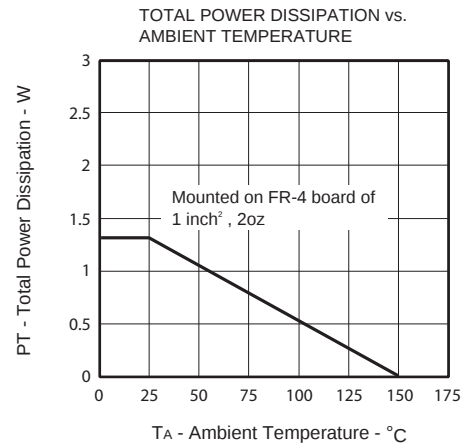
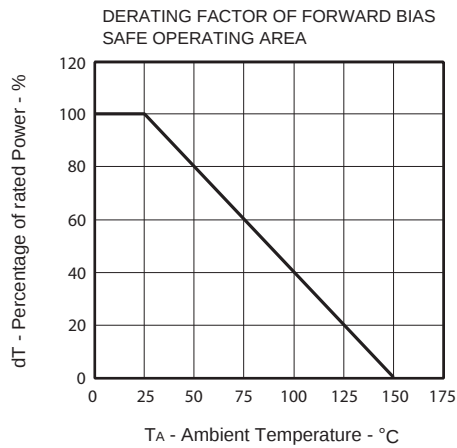
Symbol	Parameter		Limit	Units
V _{DS}	Drain-Source Voltage		20	V
V _{GS}	Gate-Source Voltage		±12	V
I _D	Drain Current-Continuous ^c	T _A =25°C	12	A
		T _A =70°C	9.6	A
I _{DM}	-Pulsed ^{a c}		72	A
P _D	Maximum Power Dissipation	T _A =25°C	1.32	W
		T _A =70°C	0.84	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

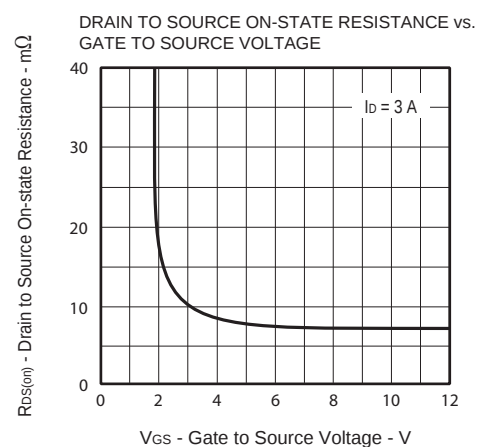
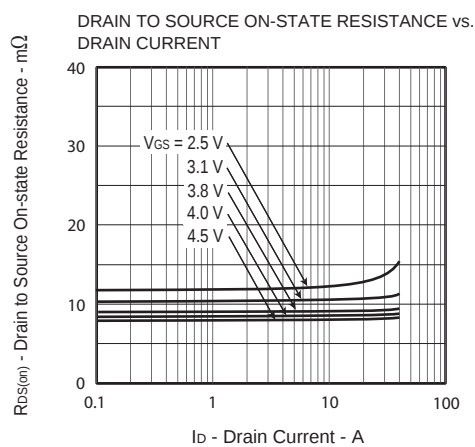
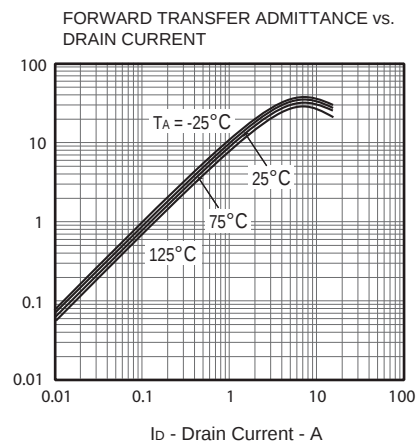
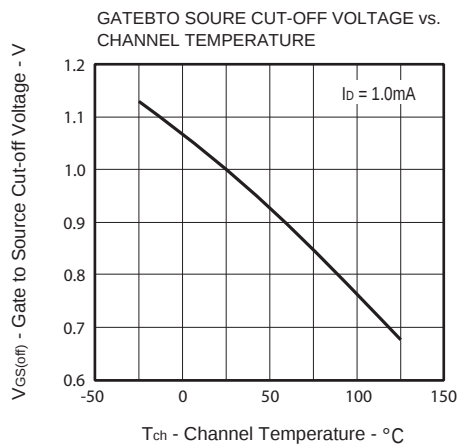
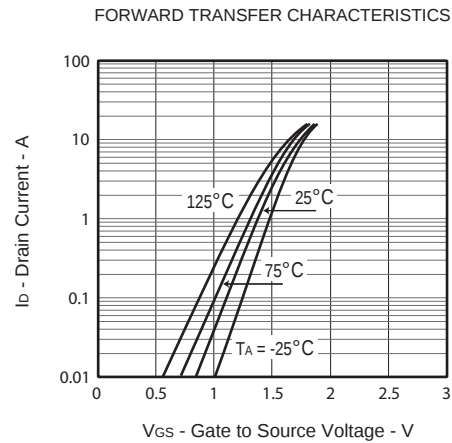
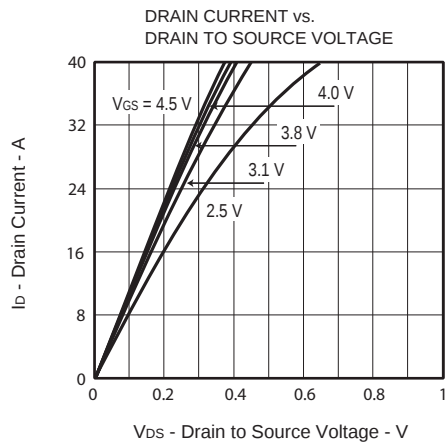
THERMAL CHARACTERISTICS

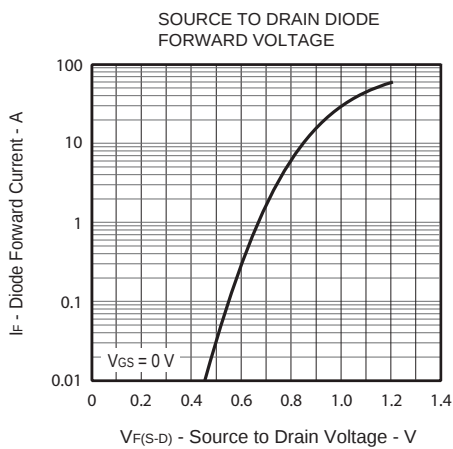
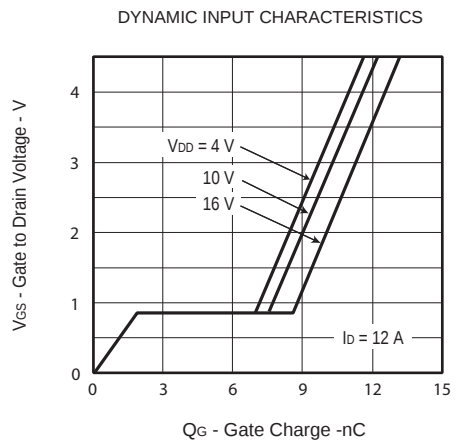
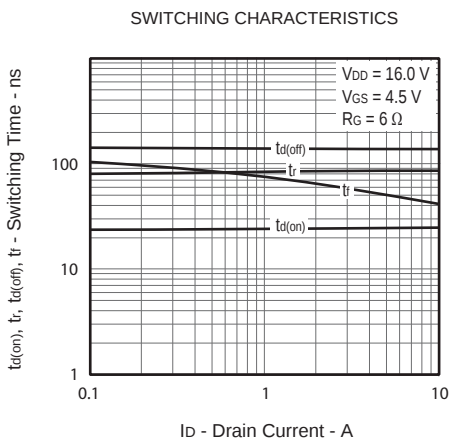
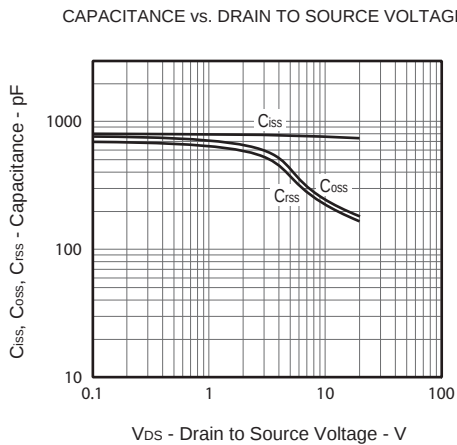
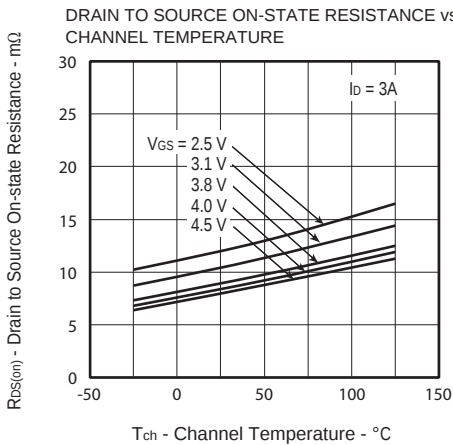
R _{θJA}	Thermal Resistance, Junction-to-Ambient	95	°C/W
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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±8V , V _{DS} =0V			±1	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =1mA	0.5	1.0	1.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V , I _D =3A	6.5	8.0	9.5	m ohm
		V _{GS} =4.0V , I _D =3A	7.0	8.5	9.8	m ohm
		V _{GS} =3.8V , I _D =3A	7.5	9.0	10.5	m ohm
		V _{GS} =3.1V , I _D =3A	8.0	10.5	12.5	m ohm
		V _{GS} =2.5V , I _D =3A	9.5	12.0	15.0	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =6A		28		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =10V,V _{GS} =0V f=1.0MHz		772		pF
C _{OSS}	Output Capacitance			253		pF
C _{RSS}	Reverse Transfer Capacitance			229		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =16V I _D =6A V _{GS} =4.5V R _{GEN} = 6 ohm		23		ns
t _r	Rise Time			84		ns
t _{D(OFF)}	Turn-Off Delay Time			123		ns
t _f	Fall Time			48		ns
Q _g	Total Gate Charge	V _{DS} =16V,I _D =12A, V _{GS} =4.5V		13.1		nC
Q _{gs}	Gate-Source Charge			1.8		nC
Q _{gd}	Gate-Drain Charge			6.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =12A		0.86	1.2	V
Notes						
a.Pulse Test:Pulse Width ≤ 10us, Duty Cycle ≤ 1%.						
b.Guaranteed by design, not subject to production testing.						
c.Drain current limited by maximum junction temperature.						
d.Mounted on FR4 Board of 1 inch ² , 2oz copper.						

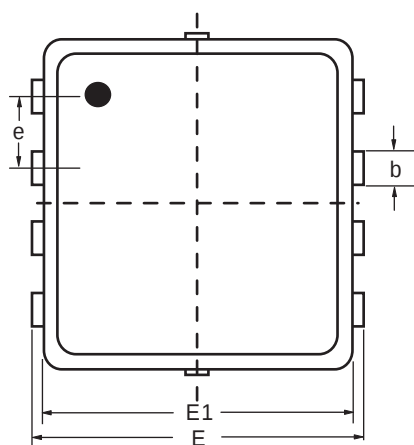




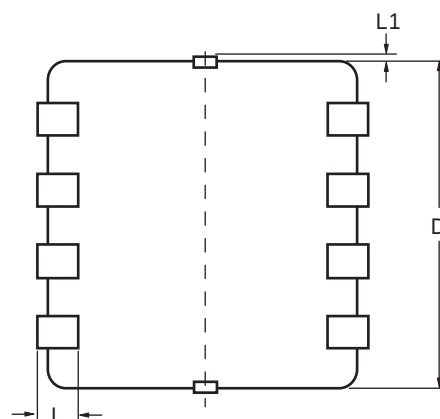


PACKAGE OUTLINE DIMENSIONS

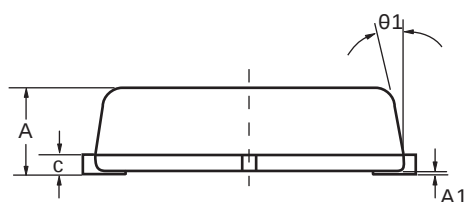
S mini 8



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOLS	MILLIMETERS		
	MIN	NOM	MAX
A	0.700	0.800	0.900
A1	0.000	—	0.050
b	0.240	0.300	0.350
c	0.080	0.152	0.250
D	2.800	2.900	3.000
E	2.700	2.800	2.900
E1	2.200	2.300	2.400
e	0.650 BSC		
L	0.200	0.375	0.450
L1	0.000	—	0.100
θ1	0°	10°	12°

TOP MARKING DEFINITION

